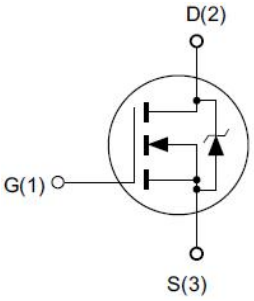
SPF5N60M/SPD5N60M

N-Channel Power MOSFET

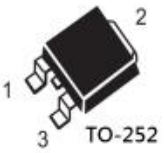
Features

- ◆ 600V, 5A, $R_{DS(ON)}$(Max.) = 2.7Ω@VGS = 10V.
- ◆ Low Crss
- ◆ Fast Switching
- ◆ 100% Avalanche Tested



Application

- ◆ Charger
- ◆ Standby Power



Absolute Maximum Ratings T_C = 25°C unless otherwise noted

Symbol	Parameter	Limit		Unit
		TO-220F	TO-252	
V_{DS}	Drain-Source Voltage [a]	600		V
V_{GS}	Gate-Source Voltage	± 30		V
I_D	Drain Current-Continuous, T_C =25°C	5		A
	Drain Current-Continuous, T_C =100°C	2.5		A
I_{DM}	Drain Current-Pulsed [b]	16		A
P_D	Maximum Power Dissipation @ T_J =25°C	33	77	W
E_{AS}	Single Pulsed Avalanche Energy [d]	200		mJ
T_J, T_{STG}	Operating and Store Temperature Range	-55 to 150		°C

Thermal Characteristics

Symbol	Parameter	Value		Unit
		TO-220F	TO-252	
$R_{\theta JC}$	Thermal Resistance, Junction-Case Max.	3.5	1.5	°C/W
$R_{\theta JA}$	Thermal Resistance Junction-Ambient Max	62.5	110	°C/W

Electrical Characteristics T_J = 25°C unless otherwise noted

Off Characteristics

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS} = 0V, I_D = 250μA	600	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 600V, V_{GS} = 0V	-	-	1	μA
I_{GSS}	Forward Gate Body Leakage Current	V_{DS} = 0V, V_{GS} = ±30V	-	-	±100	nA

On Characteristics

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
V_{GS}(th)	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D =250μA	2	-	4	V
R_{DS}(on)	Static Drain-Source On-Resistance [c]	V_{GS} = 10V, I_D =2A	-	2.1	2.7	Ω

Dynamic Characteristics

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
Ciss	Input Capacitance	V_{DS} = 25V, V_{GS} = 0V, f = 1.0MHz	-	610	-	pF
Coss	Output Capacitance		-	53	-	pF
Crss	Reverse Transfer Capacitance		-	3.5	-	pF

On Characteristics

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-On Delay Time	V_{DD} = 325V, I_D =4A, R_G = 25Ω,V_{GS}=10V	-	12.7	-	ns
t_r	Turn-On Rise Time		-	17.4	-	ns
$t_{d(off)}$	Turn-Off Delay Time		-	30.9	-	ns
t_f	Turn-Off Fall Time		-	10.5	-	ns
Qg	Total Gate Charge	V_{DS} = 520V, I_D =4A, V_{GS} = 10V	-	14.2		nC
Qgs	Gate-Source Charge		-	5.5	-	nC
Qgd	Gate-Drain Charge		-	3.8	-	nC

Drain-Source Diode Characteristics

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
I_S	Drain-Source Diode Forward Continuous Current	V_{GS} = 0V	-	-	4	A
I_{SM}	Maximum Pulsed Current	V_{GS} = 0V	-	-	16	A
V_{SD}	Drain-Source Diode Forward Voltage	V_{GS} = 0V, I_S = 4A	-	-	1.4	V
Trr	Body Diode Reverse Recovery Time	di/dt=100A/us I_F=4A	-	264	-	ns

Notes:

a. T_J=+25 ℃ to +150 ℃

b. Repetitive rating; pulse width limited by maximum junction temperature.

c. Pulse width≦300us; duty cycle≦2%

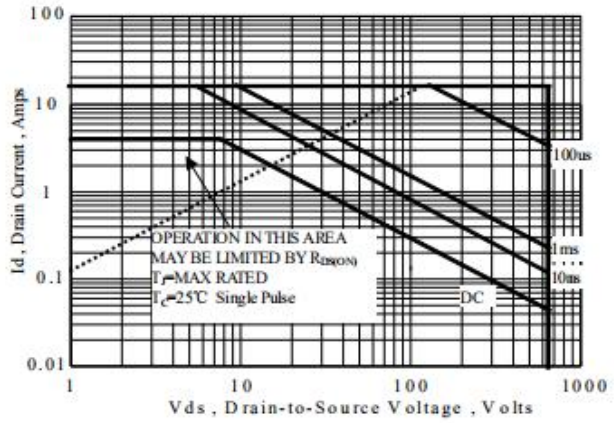


Figure 1 Maximum Safe Operating Area

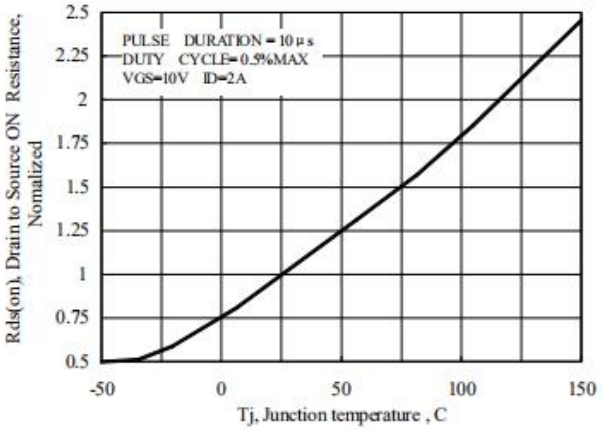


Figure 2. Normalized On-Resistance Variation with Temperature

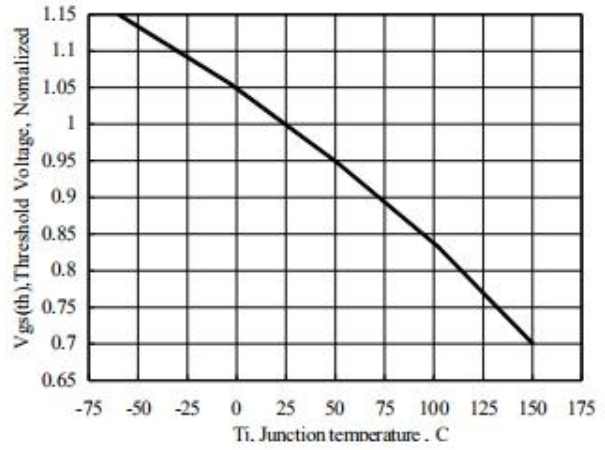


Figure 3. Typical Theshold Voltage vs Junction Temperature

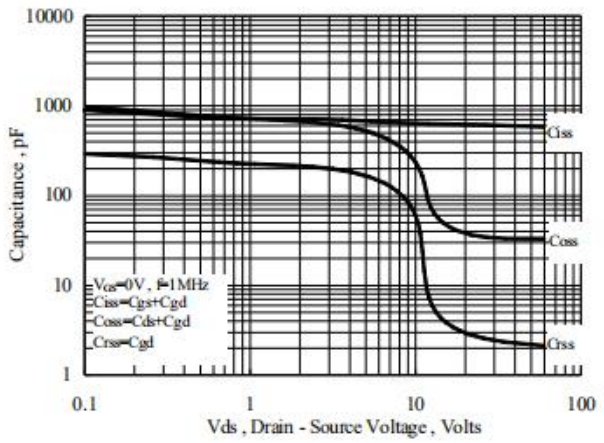


Figure 4. Capacitance Characteristics

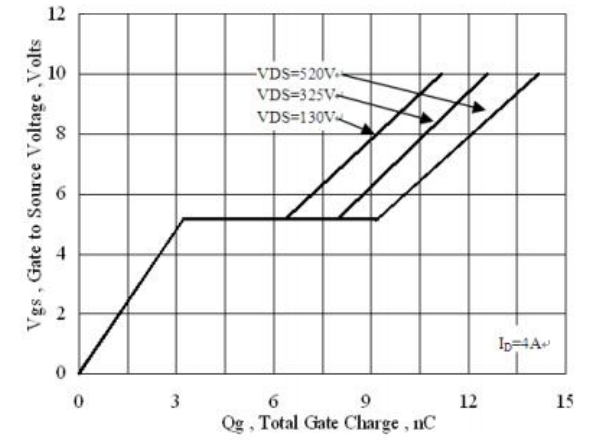


Figure 5. Gate Charge Characteristics

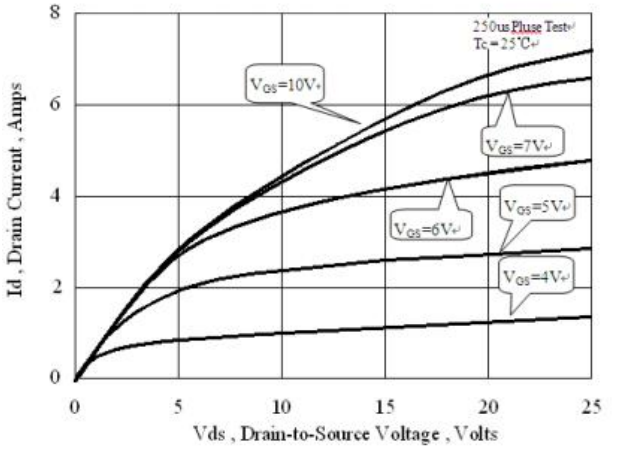


Figure 6. On-State Characteristics

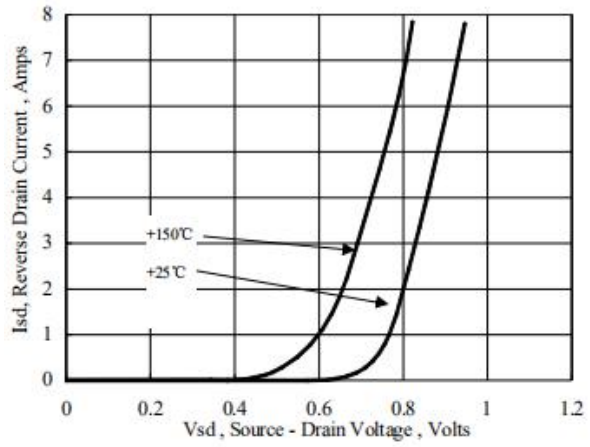


Figure 7. Typical Body Diode Transfer Characteristics

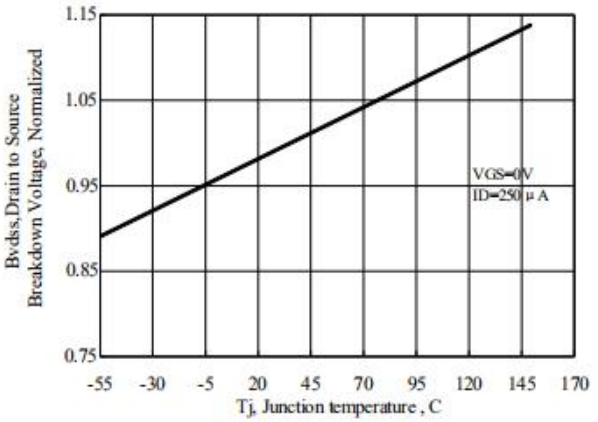


Figure 8. Typical Breakdown Voltage vs Junction Temperature

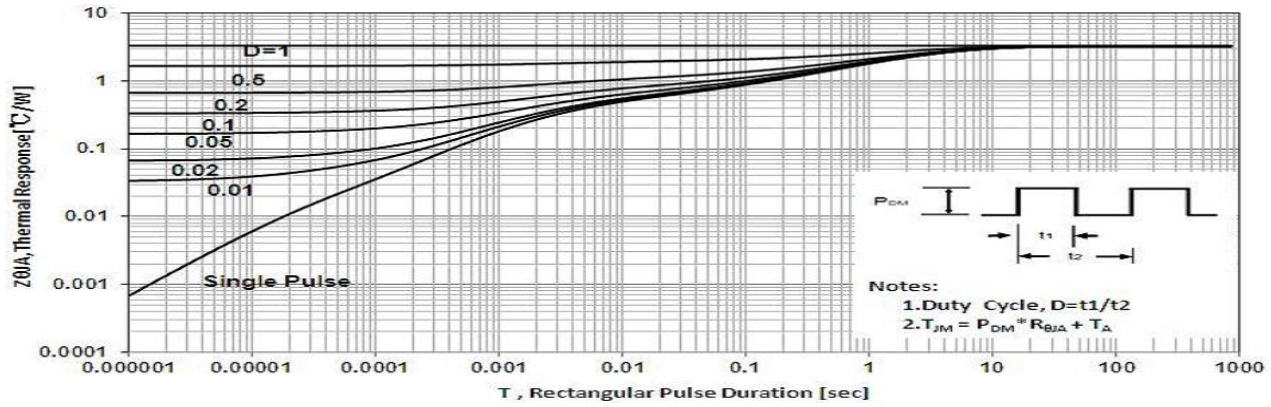


Figure 9. Normalized Effective Transient Thermal Impedance With Pulse Duration(TO-220F)

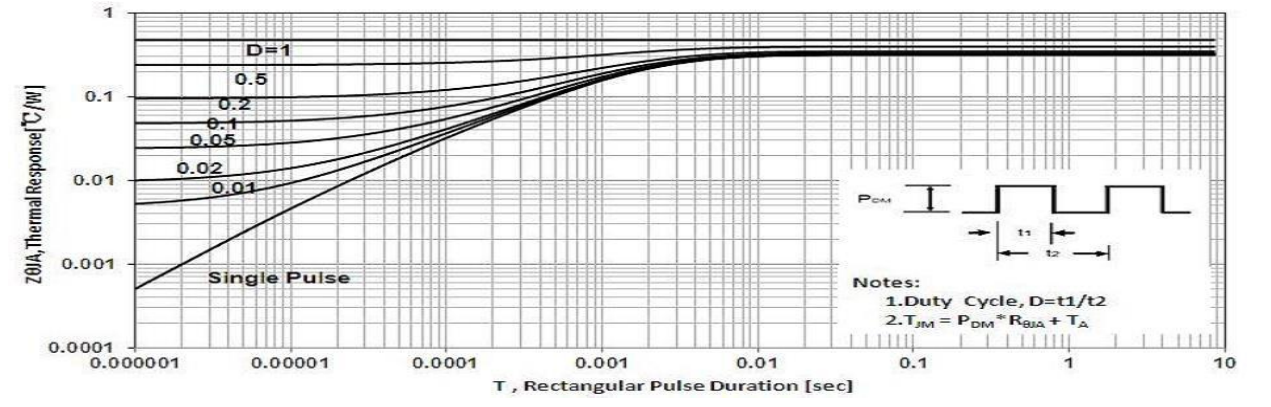


Figure 10 .Normalized Effective Transient Thermal Impedance With Pulse Duration(TO-252)